Fig. 2.1 The first bipolar transistor (point-contact transistor) invented at Bell Laboratories in 1947. (Photo courtesy of Bell Laboratories)
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Fig. 6.5 The waffle MOSFET gives the same subthreshold characteristics as compared with the conventional multi-finger MOSFET.
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Fig. 6.8 Comparison of the small signal gain of the waffle MOSFET with the conventional multi-finger type at various supply voltage $V_{DD}$. 

$V_{GS} = 0.65 V$, $I_{DS} \approx 1.0 mA$ 
$f = 3 GHz$ 

$W_{Manh} = 206 \mu m; W_{non-Manh} = 210 \mu m$;
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